

**SANYO**

No.3574

**2SK1436**

N-Channel MOS Silicon FET

Very High-Speed  
Switching Applications**Features**

- Low ON-state resistance.
- Very high-speed switching.
- Converters.
- Micaless package facilitating easy mounting.

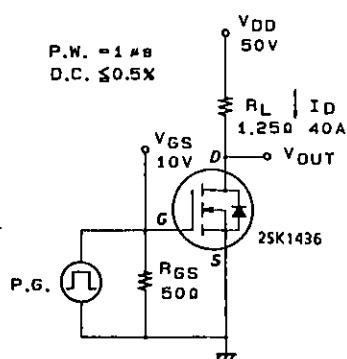
**Absolute Maximum Ratings at Ta=25°C**

			unit
Drain to Source Voltage	V <sub>DSS</sub>	100	V
Gate to Source Voltage	V <sub>GSS</sub>	±20	V
Drain Current(DC)	I <sub>D</sub>	50	A
Drain Current(Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	200 A
Allowable Power Dissipation	P <sub>D</sub>	T <sub>c</sub> =25°C	80 W
			3.0 W
Channel Temperature	T <sub>ch</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

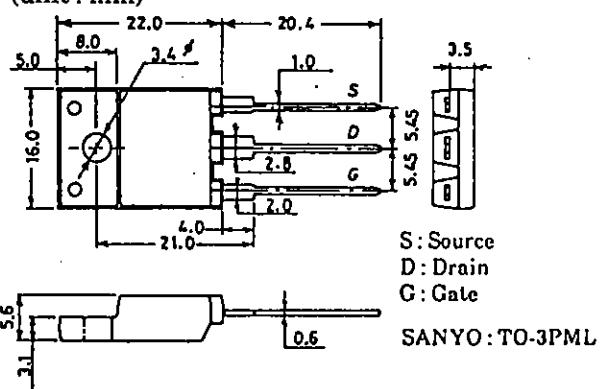
**Electrical Characteristics at Ta=25°C**

			min	typ	max	unit
D-S Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> =1mA, V <sub>GS</sub> =0	100			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =100V, V <sub>GS</sub> =0		100		μA
Gate to Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0		±100		nA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	1.5		2.5	V
Forward Transfer Admittance	Y <sub>fs</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =40A	27	45		S
Static Drain to Source on State Resistance	R <sub>DS(on)</sub>	I <sub>D</sub> =40A, V <sub>GS</sub> =10V		0.023	0.035	Ω
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =20V, f=1MHz	4800			pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =20V, f=1MHz	1400			pF
Reverse Transfer Capacitance	C <sub>rss</sub>	V <sub>DS</sub> =20V, f=1MHz	400			pF
Turn-ON Delay Time	t <sub>d(on)</sub>			45		ns
Rise Time	t <sub>r</sub>	I <sub>D</sub> =40A, V <sub>GS</sub> =10V		195		ns
Turn-OFF Delay Time	t <sub>d(off)</sub>	V <sub>DD</sub> =50V, R <sub>GS</sub> =50Ω		560		ns
Fall Time	t <sub>f</sub>			240		ns
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =50A, V <sub>GS</sub> =0			1.8	V

(Note) Be careful in handling the 2SK1436 because it has no protection diode between gate and source.

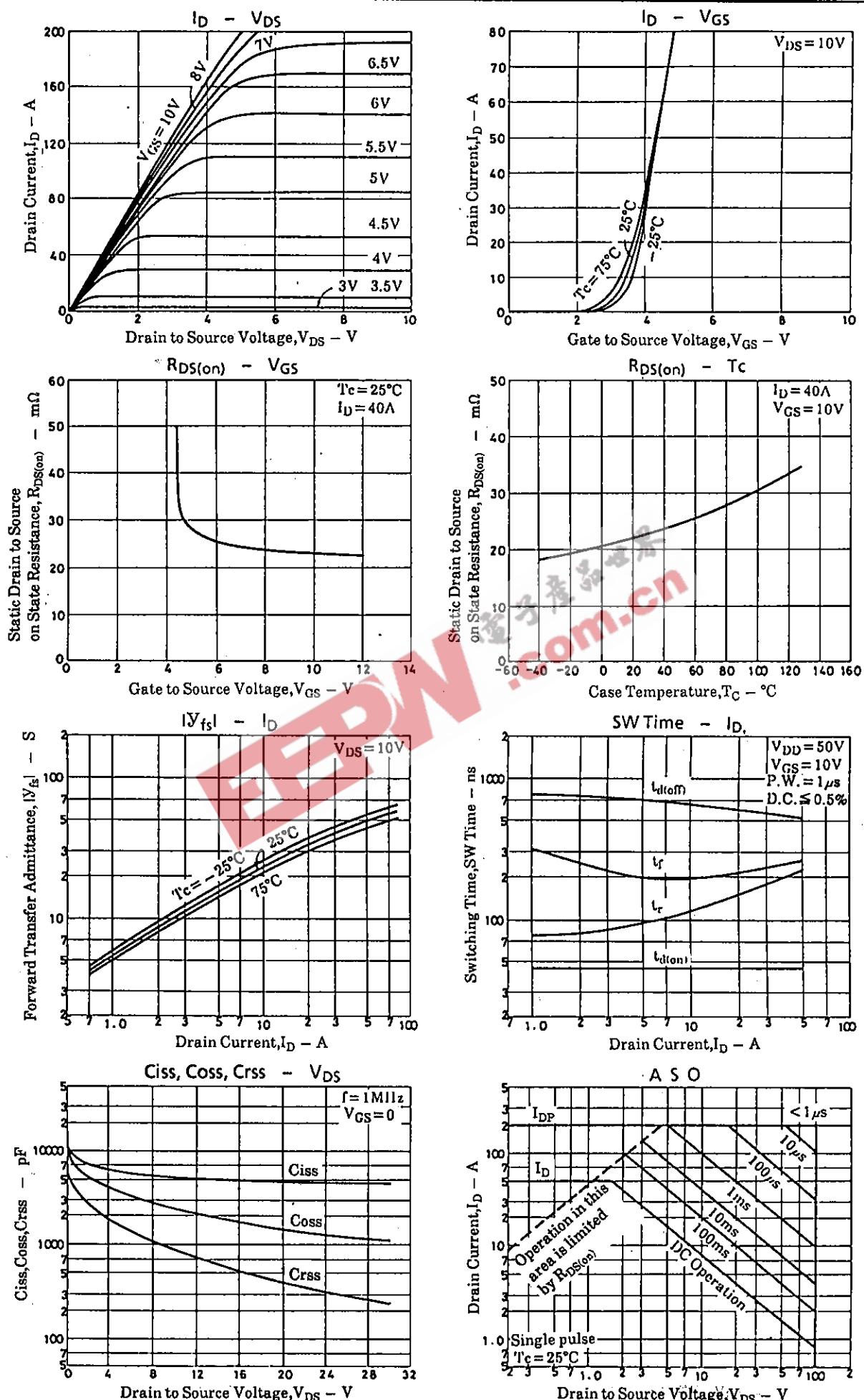
**Switching Time Test Circuit****Package Dimensions 2076**

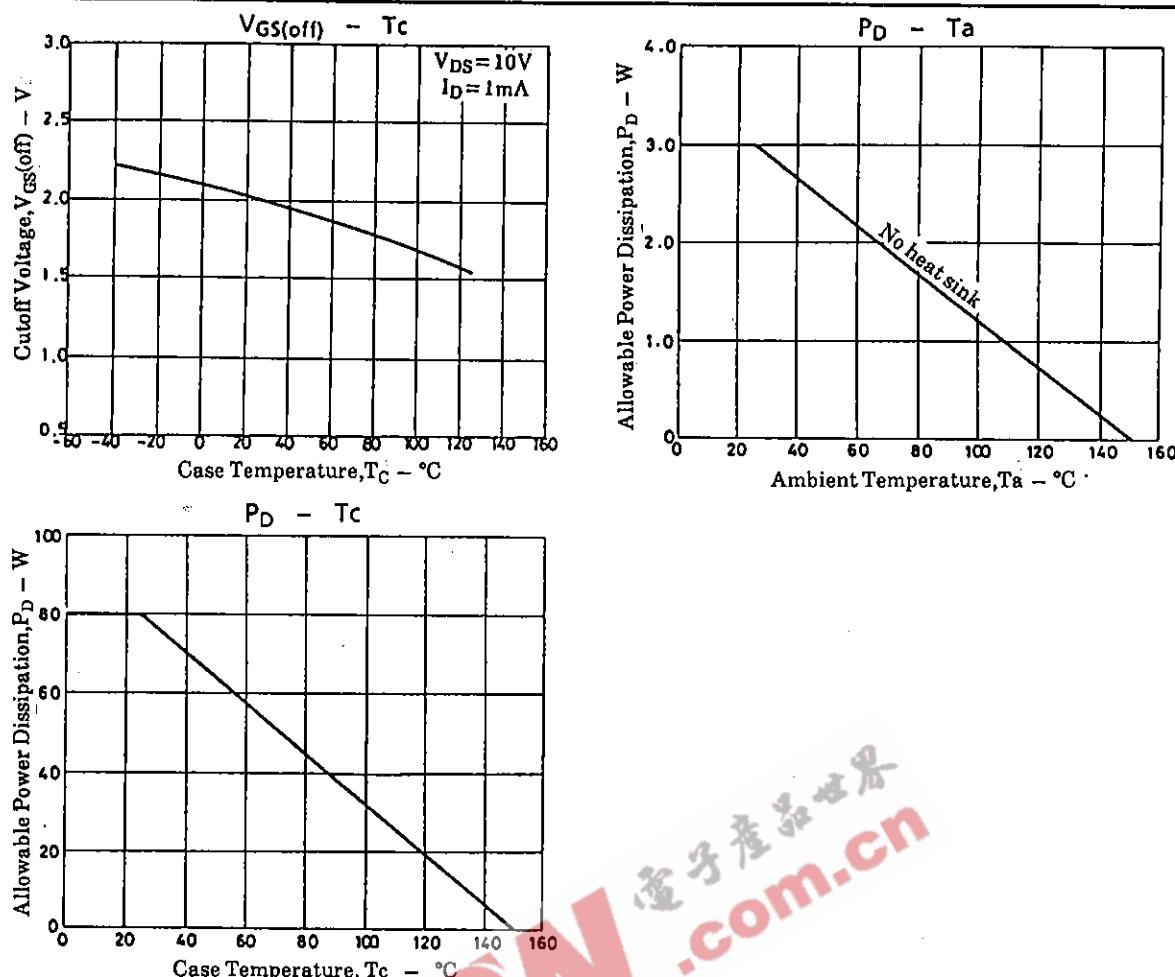
(unit : mm)

S: Source  
D: Drain  
G: Gate

SANYO: TO-3PML

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